

**IN THE CLAIMS**

This is a complete and current listing of the claims, marked with status identifiers in parentheses. The following listing of claims will replace all prior versions and listings of claims in the application.

1. (Original) A semiconductor polishing composition comprising:

fumed silica, the semiconductor polishing composition being an aqueous dispersion solution of fumed silica,

wherein the number of particles of fumed silica having a particle diameter of 0.5  $\mu\text{m}$  or more is 600,000 pieces/ml or less and the number of particles of fumed silica having a particle diameter of 1  $\mu\text{m}$  or more is 6000 pieces/ml or less.

2. (Original) The semiconductor polishing composition of claim 1, wherein the semiconductor polishing composition has the number of fumed silica particles that have a particle diameter of 0.5  $\mu\text{m}$  or more in a range of 10,000 to 600,000 pieces/ml.

3. (Currently Amended) The semiconductor polishing composition of claim 1—~~or 2~~, wherein the semiconductor polishing composition has the number of fumed silica particles that have a particle diameter of 1  $\mu\text{m}$  or more in a range of 500 to 6000 pieces/ml.

4. (Currently Amended) The semiconductor polishing composition of ~~any one of claims 1 to 3~~, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

5. (Currently Amended) The semiconductor polishing composition of ~~any one of claims 1 to 4~~, wherein the aqueous

dispersion solution of fumed silica is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

6. (Original) The semiconductor polishing composition of claim 5, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.

7. (New) The semiconductor polishing composition of claim 2, wherein the semiconductor polishing composition has the number of fumed silica particles that have a particle diameter of 1  $\mu\text{m}$  or more in a range of 500 to 6000 pieces/ml.

8. (New) The semiconductor polishing composition of claim 2, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

9. (New) The semiconductor polishing composition of claim 3, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

10. (New) The semiconductor polishing composition of claim 7, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

11. (New) The semiconductor polishing composition of claim 2, wherein the aqueous dispersion solution of fumed silica is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

12. (New) The semiconductor polishing composition of claim 3, wherein the aqueous dispersion solution of fumed

silica is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

13. (New) The semiconductor polishing composition of claim 4, wherein the aqueous dispersion solution of fumed silica is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

14. (New) The semiconductor polishing composition of claim 11, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.

15. (New) The semiconductor polishing composition of claim 12, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.

16. (New) The semiconductor polishing composition of claim 13, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.